

* * * * * * * * * Welcome to STN International * * * * * * * * *

<u>NEWS 1</u>	Web Page URLs for STN Seminar Schedule - N. America
<u>NEWS 2</u>	"Ask CAS" for self-help around the clock
<u>NEWS 3</u> FEB 28	PATDPAFULL - New display fields provide for legal status data from INPADOC
<u>NEWS 4</u> FEB 28	BABS - Current-awareness alerts (SDIs) available
<u>NEWS 5</u> MAR 02	GBFULL: New full-text patent database on STN
<u>NEWS 6</u> MAR 03	REGISTRY/ZREGISTRY - Sequence annotations enhanced
<u>NEWS 7</u> MAR 03	MEDLINE file segment of TOXCENTER reloaded
<u>NEWS 8</u> MAR 22	KOREAPAT now updated monthly; patent information enhanced
<u>NEWS 9</u> MAR 22	Original IDE display format returns to REGISTRY/ZREGISTRY
<u>NEWS 10</u> MAR 22	PATDPASPC - New patent database available
<u>NEWS 11</u> MAR 22	REGISTRY/ZREGISTRY enhanced with experimental property tags
<u>NEWS 12</u> APR 04	EPFULL enhanced with additional patent information and new fields
<u>NEWS 13</u> APR 04	EMBASE - Database reloaded and enhanced
<u>NEWS 14</u> APR 18	New CAS Information Use Policies available online
<u>NEWS 15</u> APR 25	Patent searching, including current-awareness alerts (SDIs), based on application date in CA/CAplus and USPATFULL/USPAT2 may be affected by a change in filing date for U.S. applications.
<u>NEWS 16</u> APR 28	Improved searching of U.S. Patent Classifications for U.S. patent records in CA/CAplus
<u>NEWS 17</u> MAY 23	GBFULL enhanced with patent drawing images
<u>NEWS 18</u> MAY 23	REGISTRY has been enhanced with source information from CHEMCATS
<u>NEWS 19</u> JUN 06	THE Analysis Edition of STN Express with Discover! (Version 8.0 for Windows) now available
<u>NEWS 20</u> JUN 13	RUSSIAPAT: New full-text patent database on STN
<u>NEWS 21</u> JUN 13	FRFULL enhanced with patent drawing images
<u>NEWS 22</u> JUN 27	MARPAT displays enhanced with expanded G-group definitions and text labels
<u>NEWS 23</u> JUL 01	MEDICONF removed from STN
<u>NEWS 24</u> JUL 07	STN Patent Forums to be held in July 2005
<u>NEWS 25</u> JUL 13	SCISEARCH reloaded
<u>NEWS 26</u> JUL 20	Powerful new interactive analysis and visualization software, STN AnaVist, now available
<u>NEWS EXPRESS</u>	JUNE 13 CURRENT WINDOWS VERSION IS V8.0, CURRENT MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP), AND CURRENT DISCOVER FILE IS DATED 13 JUNE 2005
<u>NEWS HOURS</u>	STN Operating Hours Plus Help Desk Availability
<u>NEWS INTER</u>	General Internet Information
<u>NEWS LOGIN</u>	Welcome Banner and News Items
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*ENCOMPLIT - EnCompass Literature File 1964-present (Supporters)
 *ENCOMPLIT2 - EnCompass Literature File 1964-Present (Non-Supporters)
 *ENCOMPPAT - EnCompass Patent File 1964-present (Supporters)
 *ENCOMPPAT2 - EnCompass Patent File 1964-Present (Non-Supporters)

* The files listed above are temporarily unavailable.

FILE 'HOME' ENTERED AT 09:29:59 ON 27 JUL 2005

=> file inspec

COST IN U.S. DOLLARS	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'INSPEC' ENTERED AT 09:30:10 ON 27 JUL 2005

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FILE LAST UPDATED: 25 JUL 2005 <20050725/UP>

FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN
 THE BASIC INDEX >>>

=> s copper interdiffusion

145933 COPPER
 14603 INTERDIFFUSION

L1 1 COPPER INTERDIFFUSION
 (COPPER (W) INTERDIFFUSION)

=> d 11

L1 ANSWER 1 OF 1 INSPEC (C) 2005 IEE on STN

Full Text

AN 1991:3969613 INSPEC DN A91122523
 TI The effect of microstructure on the magnetic behavior of epitaxial cobalt layers.
 AU Mankey, G.J.; Kief, M.T.; Willis, R.F. (Dept. of Phys., Pennsylvania State Univ., University Park, PA, USA)
 SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1991) vol.9, no.3, pt.2, p.1595-8. 16 refs.
 Price: CCCC 0734-2101/91/031595-04\$01.00
 CODEN: JVTAD6 ISSN: 0734-2101
 Conference: 37th National Symposium of the American Vacuum Society.
 Toronto, Ont., Canada, 8-12 Oct 1990
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

=>

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SINCE FILE

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SO Journal of Vacuum Science & Technology A (Vacuum, Surfaces, and Films) (May-June 1991) vol.9, no.3, pt.2, p.1595-8. 16 refs.

Price: CCCC 0734-2101/91/031595-04\$01.00

CODEN: JVTAD6 ISSN: 0734-2101

Conference: 37th National Symposium of the American Vacuum Society.

Toronto, Ont., Canada, 8-12 Oct 1990

DT Conference Article; Journal

TC Experimental

CY United States

LA English

=> s copper

L2 145933 COPPER

=> s diffusion

L3 212144 DIFFUSION

=> s tin or titanium nitride

55702 TIN
 86985 TITANIUM
 31457 NITRIDE
 2283 TITANIUM NITRIDE
 (TITANIUM(W)NITRIDE)
 L4 56000 TIN OR TITANIUM NITRIDE

=> s 12 and 13 and 14
 L5 1025 L2 AND L3 AND L4

=> s 13 same 12
 MISSING OPERATOR L3 SAME
 The search profile that was entered contains terms or
 nested terms that are not separated by a logical operator.

=> s copper diffusion
 145933 COPPER
 212144 DIFFUSION
 L6 431 COPPER DIFFUSION
 (COPPER(W)DIFFUSION)

=> s plug
 L7 9515 PLUG

=> s via
 L8 190361 VIA

=> s 16 and 17
 L9 1 L6 AND L7

=> d 19

L9 ANSWER 1 OF 1 INSPEC (C) 2005 IEE on STN

Full Text

AN 1999:6234126 INSPEC DN B1999-06-2550F-011
 TI IMP Ta/Cu seed layer technology for high-aspect-ratio via fill by
 electroplating, and its application to multilevel single damascene copper
 interconnects.
 AU Hashim, I.; Pavate, V.; Peijun Ding; Chin, B. (Appl. Mater. Inc., Santa
 Clara, CA, USA); Brown, D.; Nogami, T.
 SO Proceedings of the SPIE - The International Society for Optical
 Engineering (1998) vol.3508, p.58-64. 9 refs.
 Published by: SPIE-Int. Soc. Opt. Eng
 Price: CCCC 0277-786X/98/\$10.00
 CODEN: PSISDG ISSN: 0277-786X
 SICI: 0277-786X(1998)3508L.58:SLTH;1-K
 Conference: Multilevel Interconnect Technology II. Santa Clara, CA, USA,
 23-24 Sept 1998
 Sponsor(s): SPIE
 DT Conference Article; Journal
 TC Experimental
 CY United States
 LA English

=> s 16 and 18
 L10 24 L6 AND L8

=> d 110 1-24

L10 ANSWER 1 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:8345747 INSPEC DN A2005-10-8160B-037; B2005-05-2530F-018
 TI Oxidation mechanism of ionic transport of copper in SiO₂ dielectrics.
 AU Willis, B.G. (Dept. of Chem. Eng., Delaware Univ., Newark, DE, USA); Lang, D.V.
 SO Thin Solid Films (22 Nov. 2004) vol.467, p.284-93. 29 refs.
 Published by: Elsevier
 Price: CCCC 0040-6090/2004/\$30.00
 CODEN: THSFAP ISSN: 0040-6090
 SICI: 0040-6090(20041122)467L.284:OMIT;1-3
 DT Journal
 TC Experimental
 CY Switzerland
 LA English

L10 ANSWER 2 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7997827 INSPEC DN A2004-15-8235-002
 TI Surface modification of SiLK(R) by graft copolymerization with 4-vinylpyridine for reduction in **copper diffusion**.
 AU Zhu, Y.Q.; Kang, E.T.; Neoh, K.G. (Dept. of Chem. & Envion. Eng., Nat. Univ. of Singapore, Singapore); Chan, L.; Lai, D.M.Y.; Huan, A.C.H.
 SO Applied Surface Science (30 March 2004) vol.225, no.1-4, p.144-55. 42 refs.
 Published by: Elsevier
 Price: CCCC 0169-4332/2004/\$30.00
 CODEN: ASUSEE ISSN: 0169-4332
 SICI: 0169-4332(20040330)225:1/4L.144:SMSG;1-C
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L10 ANSWER 3 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2004:7883001 INSPEC DN B2004-04-2550F-026
 TI The application of ALD WNxCy as a **copper diffusion barrier**.
 AU Smith, S. (Philips Semicond., XXX, France); Book, G.; Li, W.M.; Sun, Y.M.; Gillespie, P.; Tuominen, M.; Pfeifer, K.
 SO Proceedings of the IEEE 2003 International Interconnect Technology Conference (Cat. No.03TH8695)
 Piscataway, NJ, USA: IEEE, 2003. p.135-7 of 271 pp. 6 refs.
 Conference: Burlingame, CA, USA, 2-4 June 2003
 Sponsor(s): IEEE Electron Devices Soc
 Price: CCCC 0 7803 7797 4/2003/\$17.00
 ISBN: 0-7803-7797-4
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L10 ANSWER 4 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2003:7792364 INSPEC DN B2004-01-2550F-010

TI Electromigration improvement with PDL TiN(Si) barrier in copper dual
 damascene structures.
 AU Alers, G.B.; Vijayendran, A. (Novellus Syst., San Jose, CA, USA);
 Gillespie, P.; Chen, L.; Cox, H.; Lam, K.; Augur, R.; Shannon, K.;
 Pfeifer, S.; Danek, M.
 SO 2003 IEEE International Reliability Physics Symposium Proceedings 41st
 Annual (Cat. No.03CH37400)
 Piscataway, NJ, USA: IEEE, 2003. p.151-5 of 645 pp. 7 refs.
 Conference: Dallas, TX, USA, 30 March-4 April 2003
 Sponsor(s): IEEE Electron Devices Soc.; IEEE Reliability Soc
 Price: CCCC 0-7803-7649-8/03/\$17.00
 ISBN: 0-7803-7649-8
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L10 ANSWER 5 OF 24 INSPEC (C) 2005 IEE on STN

 
 AN 2003:7728857 INSPEC DN A2003-20-6860-018; B2003-10-2550F-035
 TI Copper grain boundary diffusion in electroless deposited cobalt based
 films and its influence on diffusion barrier integrity for copper
 metallization.
 AU Kohn, A.; Eizenberg, M. (Dept. of Mater. Eng., Technion-Israel Inst. of
 Technol., Haifa, Israel); Shacham-Diamond, Y.
 SO Journal of Applied Physics (1 Sept. 2003) vol.94, no.5, p.3015-24. 31
 refs.
 Doc. No.: S0021-8979(03)04318-4
 Published by: AIP
 Price: CCCC 0021-8979/2003/94(5)/3015(10)/\$20.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(20030901)94:5L.3015:CGBD;1-7
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 6 OF 24 INSPEC (C) 2005 IEE on STN

 
 AN 2003:7594518 INSPEC DN A2003-11-7920N-036; B2003-05-2550B-043
 TI SIMS depth profile of copper in low-k dielectrics under electron
 irradiation for charge compensation.
 AU Yamada, K.; Fujiyama, N.; Sameshima, J.; Kamoto, R.; Karen, A. (Toray Res.
 Center Inc., Shiga, Japan)
 SO Applied Surface Science (15 Jan. 2003) vol.203-204, p.512-15. 3 refs.
 Doc. No.: S0169-4332(02)00767-5
 Published by: Elsevier
 Price: CCCC 0169-4332/03/\$30.00
 CODEN: ASUSEE ISSN: 0169-4332
 SICI: 0169-4332(20030115)203/204L.512:SDPC;1-2
 Conference: Thirteenth International Conference on Secondary Ion Mass
 Spectrometry and Related Topics. Nara, Japan, 11-16 Nov 2001
 Sponsor(s): Microbeam Analysis 141 Committee of Japan Soc. Promotion of
 Sci.; Commemorative Assoc. Japan World Exposition (1970)
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L10 ANSWER 7 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2003:7506552 INSPEC DN A2003-04-8120S-011
 TI Synthesis of polyimides containing triazole to improve their adhesion to copper substrate.
 AU Jeonghoon Seo; Jeonghoon Kang; Kilwon Cho; Chan Eon Park (Polymer Res. Inst., Pohang Univ. of Sci. & Technol. (POSTECH), South Korea)
 SO Journal of Adhesion Science and Technology (2002) vol.16, no.13, p.1839-51. 18 refs.
 Published by: VSP
 CODEN: JATEE8 ISSN: 0169-4243
 SICI: 0169-4243(2002)16:13L.1839:SPCT;1-8
 DT Journal
 TC Experimental
 CY Netherlands
 LA English

L10 ANSWER 8 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7480317 INSPEC DN B2003-01-2550F-026
 TI Reliability of copper dual damascene influenced by pre-clean.
 AU Tokei, Zs.; Lanckmans, F.; Van den bosch, G.; Van Hove, M.; Maex, K.; Bender, H. (IMEC, Leuven, Belgium); Hens, S.; Van Landuyt, J.
 SO Proceedings of the 9th International Symposium on the Physical and Failure Analysis of Integrated Circuits (Cat. No.02TH8614) Piscataway, NJ, USA: IEEE, 2002. p.118-23 of 258 pp. 6 refs.
 Conference: Singapore, 8-12 July 2002
 Price: CCCC 0-7803-7416-9/02/\$17.00
 ISBN: 0-7803-7416-9
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L10 ANSWER 9 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2002:7426102 INSPEC DN A2002-23-8115H-032; B2002-12-2550F-068
 TI Physical and electrical characterization of ALD TiN used as a **copper diffusion** barrier in 0.25 mu m, dual damascene backend structures.
 AU Smith, S.R. (Philips Semicond. Assignees, Int. Sematech, Austin, TX, USA); Elers, K.E.; Jacobs, T.; Blaschke, V.; Pfeifer, K.
 SO Advanced Metallization Conference 2001 (AMC 2001). Proceedings of the Conference
 Editor(s): McKerrow, A.J.; Shacham-Diamand, Y.; Zaima, S.; Ohba, T. Warrendale, PA, USA: Mater. Res. Soc, 2001. p.593-5 of xxii+719 pp. 3 refs.
 Conference: Montreal, Que., Canada, 29-31 Oct 2001
 ISBN: 1-55899-670-2
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L10 ANSWER 10 OF 24 INSPEC (C) 2005 IEE on STN

Full Text

AN 2001:7078401 INSPEC DN A2001-23-6630J-009; B2001-12-2520C-012
 TI Study of copper silicide retardation effects on **copper diffusion** in silicon.
 AU Lee, C.S.; Gong, H. (Dept. of Mater. Sci., Nat. Univ. of Singapore, Kent Ridge, Singapore); Liu, R.; Wee, A.T.S.; Cha, C.L.; See, A.; Chan, L.
 SO Journal of Applied Physics (15 Oct. 2001) vol.90, no.8, p.3822-4. 7 refs.
 Doc. No.: S0021-8979(01)04505-4
 Published by: AIP
 Price: CCCC 0021-8979/2001/90(8)/3822(3)/\$18.00
 CODEN: JAPIAU ISSN: 0021-8979
 SICI: 0021-8979(20011015)90:8L.3822:SCSR;1-Y
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 11 OF 24 INSPEC (C) 2005 IEE on STN


 AN 2001:7074383 INSPEC DN B2001-12-2550F-039
 TI Properties of ion-implanted low-k organic SOG.
 AU Matsubara, N.; Mizuhara, H.; Yamashita, K.M.K.; Goto, T.; Inoue, Y.; Ibaraki, A. (Microelectron. Res. Center, Sanyo Electr. Co. Ltd., Gifu, Japan)
 SO Proceedings of the IEEE 2001 International Interconnect Technology Conference (Cat. No.01EX461)
 Piscataway, NJ, USA: IEEE, 2001. p.165-7 of iii+300 pp. 5 refs.
 Conference: Burlingame, CA, USA, 4-6 June 2001
 Sponsor(s): IEEE Electron Devices Soc
 Price: CCCC 0 7803 6678 6/2001/\$10.00
 ISBN: 0-7803-6678-6
 DT Conference Article
 TC Practical; Experimental
 CY United States
 LA English

L10 ANSWER 12 OF 24 INSPEC (C) 2005 IEE on STN

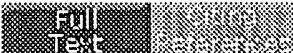

 AN 2001:6895909 INSPEC DN B2001-05-2550F-037
 TI Damascene test structures for the evaluation of barrier layer performance against **copper diffusion**.
 AU Motte, P. (STMicroelectronics, Crolles, France); Swaanen, M.; Torres, J.; Gilet, J.M.; Wyborn, G.
 SO Microelectronic Engineering (March 2001) vol.55, no.1-4, p.291-6. 2 refs.
 Doc. No.: S0167-9317(00)00459-7
 Published by: Elsevier
 Price: CCCC 0167-9317/2001/\$20.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(200103)55:1/4L.291:DTSE;1-W
 Conference: Fourth European Workshop on Materials for Advanced Metallization. Stresa, Italy, 28 Feb-1 March 2000
 Sponsor(s): STMicroelectron.; INFM; CNR-Madess
 DT Conference Article; Journal
 TC Experimental
 CY Netherlands
 LA English

L10 ANSWER 13 OF 24 INSPEC (C) 2005 IEE on STN

AN 2000:6749178 INSPEC DN B2000-12-2550F-086
 TI Overview of Cu contamination during integration in a dual damascene architecture for sub-quarter micron technology.
 AU Torres, J.; Palleau, J. (France Telecom, CNET, Meylan, France); Tardif, F.; Bernard, H.; Motte, P.; Pantel, R.; Juhel, M.
 SO Advanced Metallization Conference in 1998 (AMC 1998). Proceedings of the Conference.
 Editor(s): Sandhu, G.S.; Koerner, H.; Murakami, M.; Yasuda, Y.; Kobayashi, N.
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.645-51 of xx+784 pp. 10 refs.
 Conference: Colorado Springs, CO, USA & Tokyo, Japan, 6-8 Oct 1998 & 3-4 Sept 1998
 Sponsor(s): Continuing Educ. Eng.; Univ. Extension; Univ. California at Berkeley
 ISBN: 1-55899-484-X
 DT Conference Article
 TC Experimental
 CY United States
 LA English

L10 ANSWER 14 OF 24 INSPEC (C) 2005 IEE on STN

AN 2000:6721998 INSPEC DN B2000-11-2550F-052
 TI Reliability of dual damascene Cu metallization.
 AU Tsai, M.H.; Tsai, W.J.; Shue, S.L.; Yu, C.H.; Liang, M.S. (Taiwan Semicond. Manuf. Co. Ltd., Hsin-Chu, Taiwan)
 SO Proceedings of the IEEE 2000 International Interconnect Technology Conference (Cat. No.00EX407)
 Piscataway, NJ, USA: IEEE, 2000. p.214-16 of 277 pp. 4 refs.
 Conference: Burlingame, CA, USA, 5-7 June 2000
 Sponsor(s): IEEE Electron Devices Soc
 Price: CCCC 0 7803 6327 2/2000/\$10.00
 ISBN: 0-7803-6327-2
 DT Conference Article
 TC Practical
 CY United States
 LA English

L10 ANSWER 15 OF 24 . INSPEC (C) 2005 IEE on STN

AN 2000:6500494 INSPEC DN A2000-06-8160B-066; B2000-03-2550F-063
 TI Overview of Cu contamination during integration in a dual damascene architecture for sub-quarter micron technology.
 AU Torres, J.; Palleau, J. (FT, CNET, Meylan, France); Tardif, F.; Bernard, H.; Beverina, A.; Motte, P.; Pantel, R.; Juhel, M.
 SO Microelectronic Engineering (Jan. 2000) vol.50, no.1-4, p.425-31. 4 refs.
 Doc. No.: S0167-9317(99)00311-1
 Published by: Elsevier
 Price: CCCC 0167-9317/2000/\$20.00
 CODEN: MIENEF ISSN: 0167-9317
 SICI: 0167-9317(200001)50:1/4L.425:OCDI;1-N
 Conference: Third European Workshop on Materials for Advanced Metallization. Ostende, Belgium, 7-10 March 1999
 DT Conference Article; Journal
 TC Experimental

L10 ANSWER 19 OF 24 INSPEC (C) 2005 IEE on STN

AN 1999:6123474 INSPEC DN A1999-03-7155-021; B1999-02-2520C-013
 TI Electrical and recombination properties of copper-silicide precipitates in silicon.
 AU Istratov, A.A. (Dept. of Mater. Sci. & Miner. Eng., California Univ., Berkeley, CA, USA); Hedemann, H.; Seibt, M.; Vyvenko, O.F.; Schroter, W.; Heiser, T.; Flink, C.; Hieslmair, H.; Weber, E.R.
 SO Journal of the Electrochemical Society (Nov. 1998) vol.145, no.11, p.3889-98. 52 refs.
 Published by: Electrochem. Soc
 Price: CCCC 0013-4651/98/\$7.00
 CODEN: JESOAN ISSN: 0013-4651
 SICI: 0013-4651(199811)145:11L.3889:ERPC;1-4
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 20 OF 24 INSPEC (C) 2005 IEE on STN

AN 1998:6018767 INSPEC DN A9820-6822-008; B9810-2550F-037
 TI Barrier properties of very thin Ta and TaN layers against copper diffusion.
 AU Wang, M.T.; Lin, Y.C.; Chen, M.C. (Dept. of Electron. Eng., Nat. Chiao Tung Univ., Hsinchu, Taiwan)
 SO Journal of the Electrochemical Society (July 1998) vol.145, no.7, p.2538-45. 36 refs.
 Published by: Electrochem. Soc
 Price: CCCC 0013-4651/98/\$7.00
 CODEN: JESOAN ISSN: 0013-4651
 SICI: 0013-4651(199807)145:7L.2538:BPVT;1-8
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 21 OF 24 INSPEC (C) 2005 IEE on STN

AN 1989:3414417 INSPEC DN A89087111
 TI Formation of the 110-K superconducting phase via the amorphous state in the Bi-Sr-Ca-Cu-O system.
 AU Shi, D.; Tang, M.; Vandervoort, K.; Claus, H. (Div. of Mater. Sci., Argonne Nat. Lab., IL, USA)
 SO Physical Review B (Condensed Matter) (1 May 1989) vol.39, no.13, p.9091-8. 16 refs.
 CODEN: PRBMDO ISSN: 0163-1829
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 22 OF 24 INSPEC (C) 2005 IEE on STN

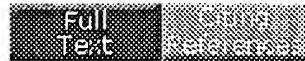
AN 1984:2304411 INSPEC DN A84088591; B84046866

TI Stress effect in Au-Si Schottky diode doped with Cu.
 AU Toyama, N. (Dept. of Electronics, Kyushu Inst. of Technol.,
 Kitakyushu-shi, Japan)
 SO Journal of Applied Physics (15 June 1984) vol.55, no.12, p.4398-403. 23
 refs.
 Price: CCCC 0021-8979/84/124398-06\$02.40
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

L10 ANSWER 23 OF 24 INSPEC (C) 2005 IEE on STN


 AN 1980:1484641 INSPEC DN A80034240
 TI On the rate-controlling step of **copper diffusion/oxidation through gold**.
 AU Tompkins, H.G.; Pinnel, M.R. (Bell Telephone Lab., Columbus, OH, USA)
 SO Journal of Applied Physics (Nov. 1979) vol.50, no.11, pt.1, p.7243-4. 5
 refs.
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Theoretical
 CY United States
 LA English

L10 ANSWER 24 OF 24 INSPEC (C) 2005 IEE on STN


 AN 1977:1116753 INSPEC DN A77080652; B77041052
 TI Relative rates of nickel diffusion and **copper diffusion through gold**
 (electrical contacts applications).
 AU Tompkins, H.G.; Pinnel, M.R. (Bell Telephone Labs., Columbus, OH, USA)
 SO Journal of Applied Physics (July 1977) vol.48, no.7, p.3144-6. 15 refs.
 CODEN: JAPIAU ISSN: 0021-8979
 DT Journal
 TC Experimental
 CY United States
 LA English

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